

CoolMOS® Power Transistor
Features

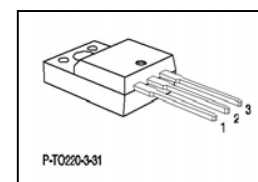
- Lowest figure-of-merit $R_{ON} \times Q_g$
- Ultra low gate charge
- Extreme dv/dt rated
- High peak current capability
- Qualified for industrial grade applications according to JEDEC¹⁾
- Pb-free lead plating; RoHS compliant; Halogen free mold compound

Product Summary

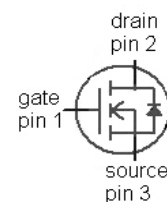
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max} @ T_j = 25^\circ C$	0.165	Ω
$Q_{g,typ}$	39	nC

CoolMOS CP is designed for:

- Hard switching SMPS topologies

PG-TO220


Type	Package	Ordering Code	Marking
IPA60R165CP	PG-TO220	SP000096437	6R165P



Maximum ratings, at $T_j = 25^\circ C$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current ²⁾	I_D	$T_C = 25^\circ C$	21	A
		$T_C = 100^\circ C$	13	
Pulsed drain current ³⁾	$I_{D,pulse}$	$T_C = 25^\circ C$	61	
Avalanche energy, single pulse	E_{AS}	$I_D = 7.9 A, V_{DD} = 50 V$	522	mJ
Avalanche energy, repetitive $t_{AR}^{3),4)}$	E_{AR}	$I_D = 7.9 A, V_{DD} = 50 V$	0.79	
Avalanche current, repetitive $t_{AR}^{3),4)}$	I_{AR}		7.9	A
MOSFET dv/dt ruggedness	dv/dt	$V_{DS} = 0 \dots 480 V$	50	V/ns
Gate source voltage	V_{GS}	static	± 20	V
		AC ($f > 1 Hz$)	± 30	
Power dissipation	P_{tot}	$T_C = 25^\circ C$	34	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 150	$^\circ C$
Mounting torque		M2.5 screws	50	Ncm

Maximum ratings, at $T_j=25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous diode forward current ²⁾	I_S	$T_C=25\text{ }^{\circ}\text{C}$	21	A
Diode pulse current ³⁾	$I_{S,pulse}$		61	
Reverse diode dv/dt ⁵⁾	dv/dt		15	V/ns

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		-		3.65	K/W
Thermal resistance, junction - ambient	R_{thJA}	leaded	-	-	80	
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	1.6 mm (0.063 in.) from case for 10 s	-	-	260	$^{\circ}\text{C}$

Electrical characteristics, at $T_j=25\text{ }^{\circ}\text{C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$	600	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=0.79\text{ mA}$	2.5	3	3.5	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=600\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ }^{\circ}\text{C}$	-	-	1	μA
		$V_{DS}=25\text{ V}, V_{GS}=0\text{ V}, T_j=150\text{ }^{\circ}\text{C}$	-	10	-	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=12\text{ A}, T_j=25\text{ }^{\circ}\text{C}$	-	0.15	0.165	Ω
		$V_{GS}=10\text{ V}, I_D=12\text{ A}, T_j=150\text{ }^{\circ}\text{C}$	-	0.40	-	
Gate resistance	R_G	$f=1\text{ MHz}, \text{open drain}$	-	1.9	-	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=100\text{ V},$ $f=1\text{ MHz}$	-	2000	-	pF
Output capacitance	C_{oss}		-	100	-	
Effective output capacitance, energy related ⁶⁾	$C_{o(er)}$	$V_{GS}=0\text{ V}, V_{DS}=0\text{ V}$ to 480 V	-	83	-	
Effective output capacitance, time related ⁷⁾	$C_{o(tr)}$		-	220	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=400\text{ V},$ $V_{GS}=10\text{ V}, I_D=12\text{ A},$ $R_G=3.3\ \Omega$	-	12	-	ns
Rise time	t_r		-	5	-	
Turn-off delay time	$t_{d(off)}$		-	50	-	
Fall time	t_f		-	5	-	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD}=400\text{ V}, I_D=12\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	9	-	nC
Gate to drain charge	Q_{gd}		-	13.0	-	
Gate charge total	Q_g		-	39	52	
Gate plateau voltage	$V_{plateau}$		-	5.0	-	V

Reverse Diode

Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=12\text{ A},$ $T_j=25\text{ °C}$	-	0.9	1.2	V
Reverse recovery time	t_{rr}	$V_R=400\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	390	-	ns
Reverse recovery charge	Q_{rr}		-	7.5	-	μC
Peak reverse recovery current	I_{rrm}		-	38	-	A

¹⁾ J-STD20 and JESD22

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Limited only by maximum temperature

⁴⁾ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR} \cdot f$.

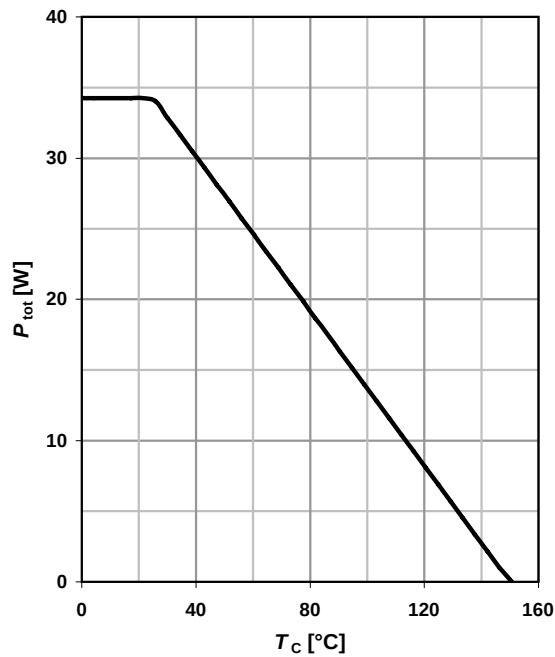
⁵⁾ $I_{SD} \leq I_D$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DClink}=400\text{ V}$, $V_{peak} < V_{(BR)DSS}$, $T_j < T_{j,max}$, identical low side and high side switch.

⁶⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⁷⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

1 Power dissipation

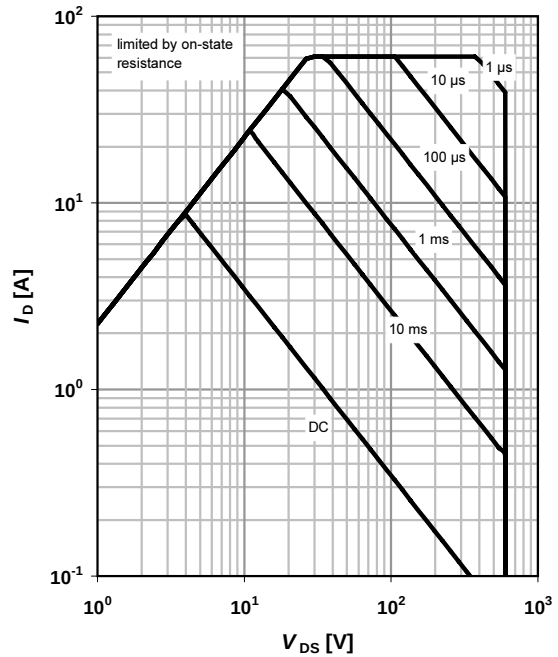
$$P_{\text{tot}} = f(T_C)$$



2 Safe operating area

$$I_D = f(V_{DS}); T_C = 25^\circ\text{C}; D = 0$$

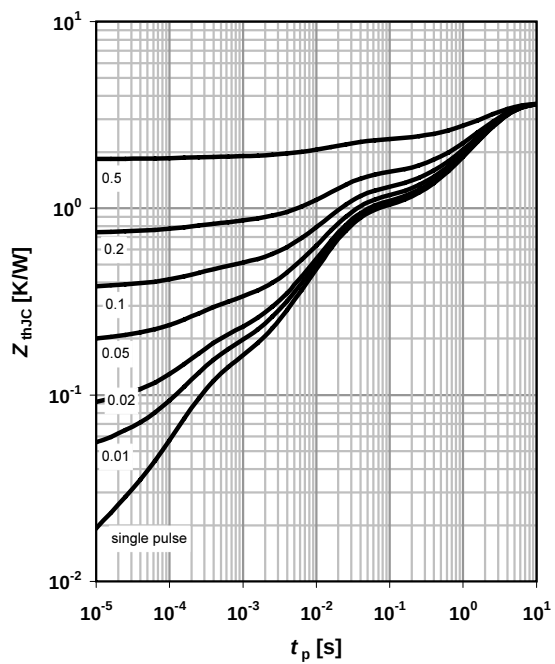
parameter: t_p



3 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

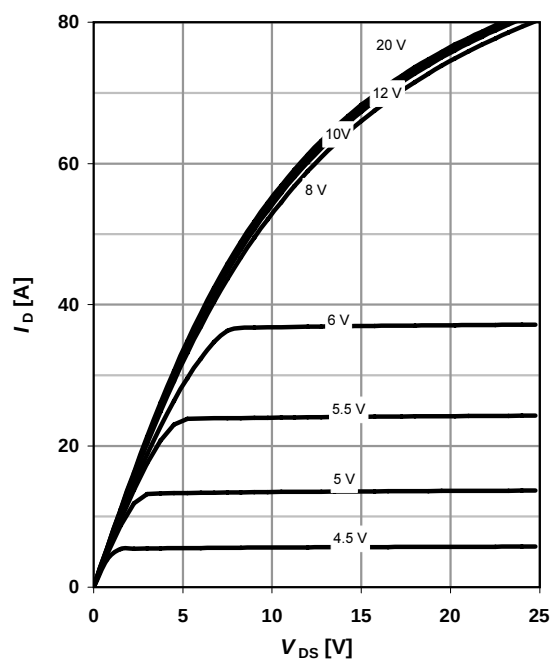
parameter: $D = t_p/T$



4 Typ. output characteristics

$$I_D = f(V_{DS}); T_J = 25^\circ\text{C}$$

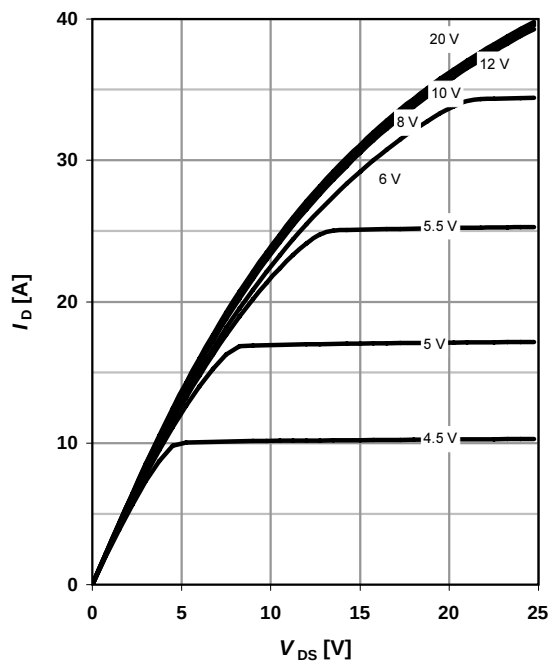
parameter: V_{GS}



5 Typ. output characteristics

$$I_D = f(V_{DS}); T_J = 150^\circ\text{C}$$

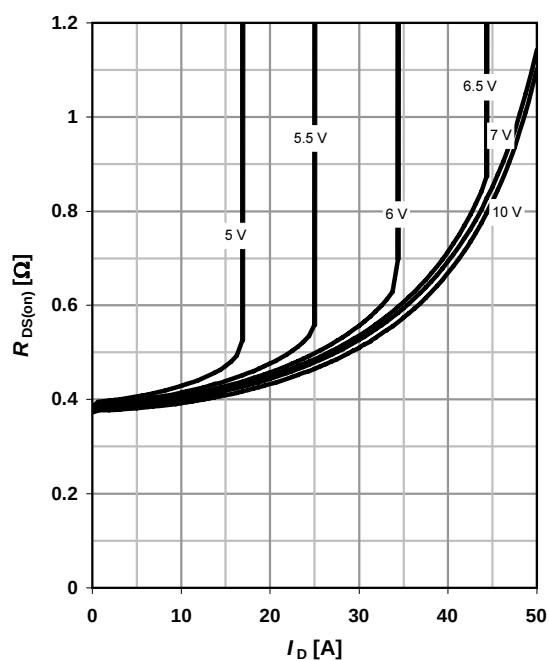
parameter: V_{GS}



6 Typ. drain-source on-state resistance

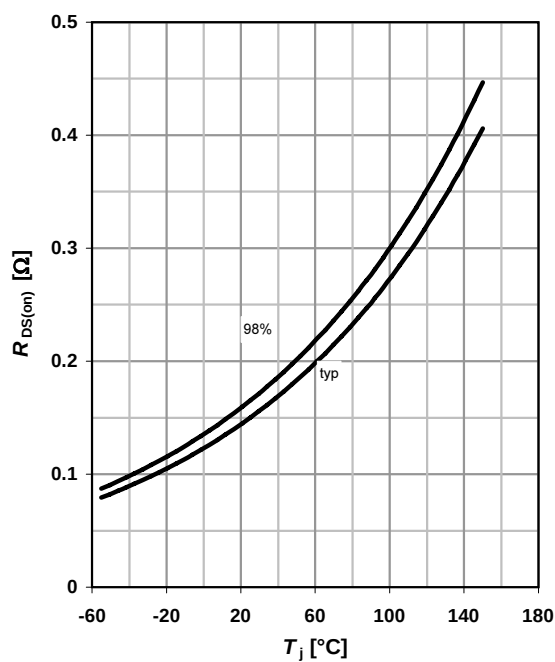
$$R_{DS(on)} = f(I_D); T_J = 150^\circ\text{C}$$

parameter: V_{GS}



7 Drain-source on-state resistance

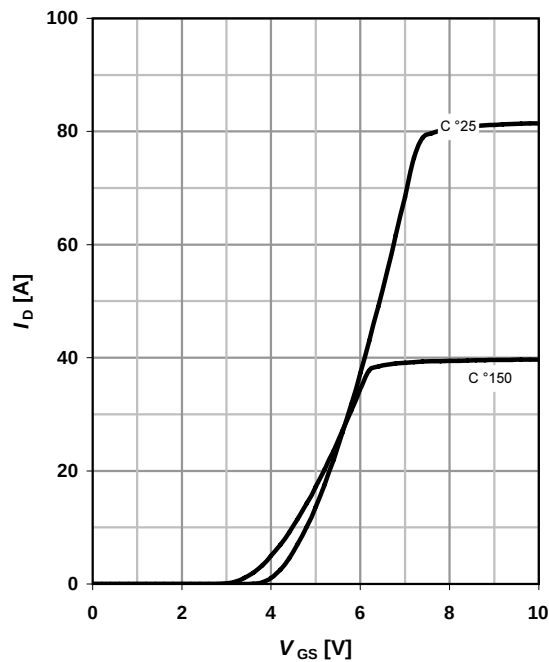
$$R_{DS(on)} = f(T_J); I_D = 12\text{ A}; V_{GS} = 10\text{ V}$$



8 Typ. transfer characteristics

$$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)\max}$$

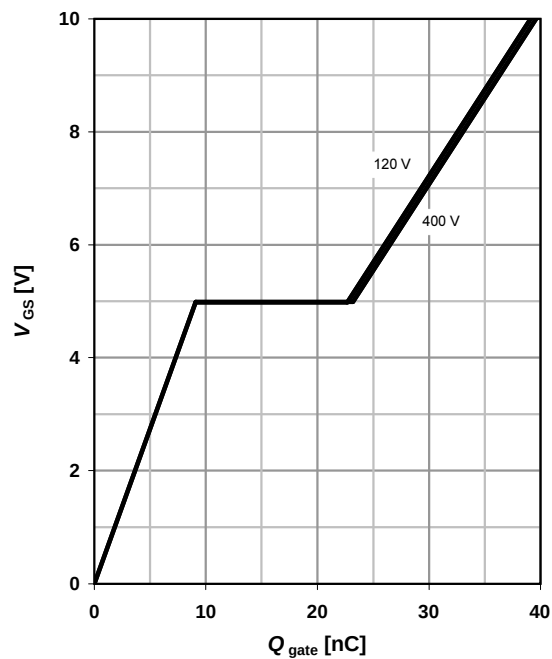
parameter: T_J



9 Typ. gate charge

$$V_{GS}=f(Q_{gate}); I_D=12\text{ A pulsed}$$

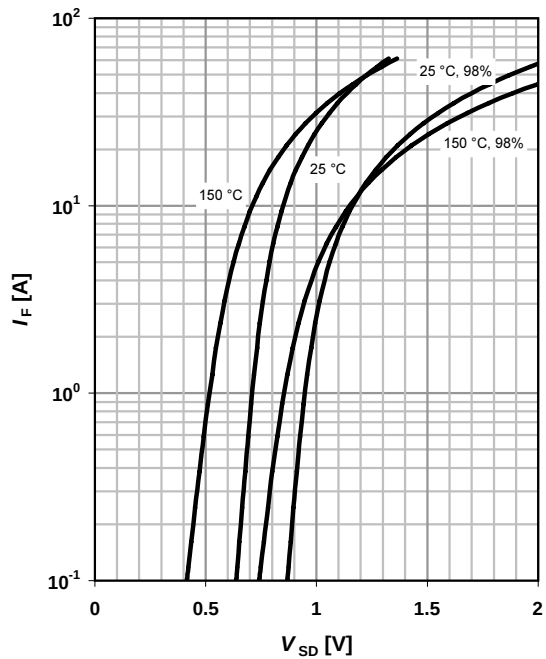
parameter: V_{DD}



10 Forward characteristics of reverse diode

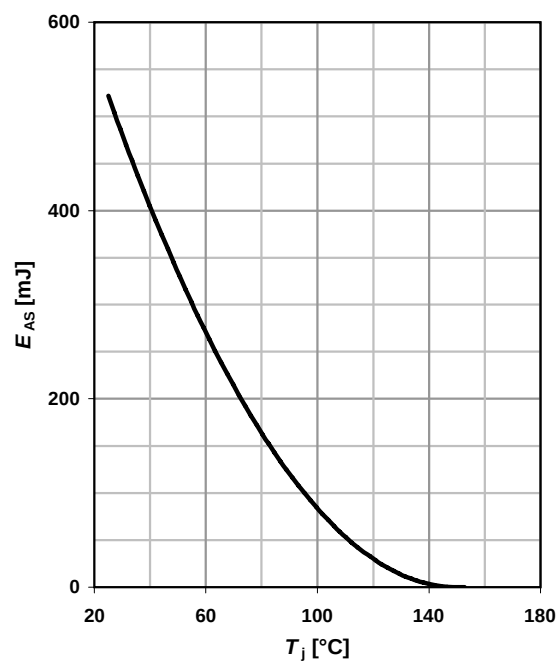
$$I_F=f(V_{SD})$$

parameter: T_j



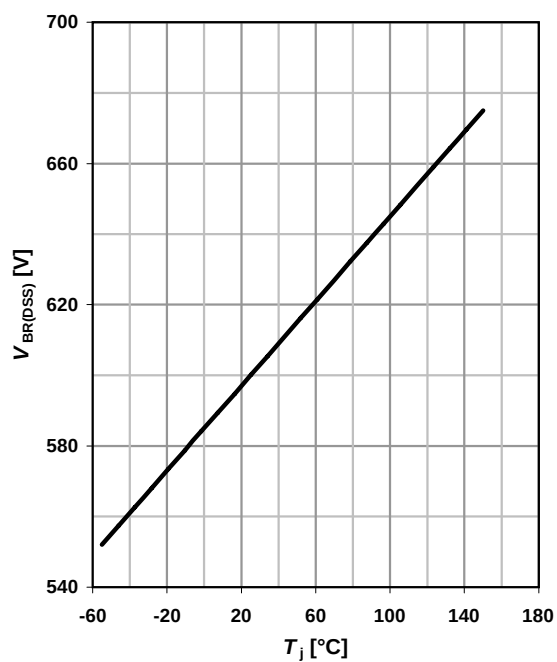
11 Avalanche energy

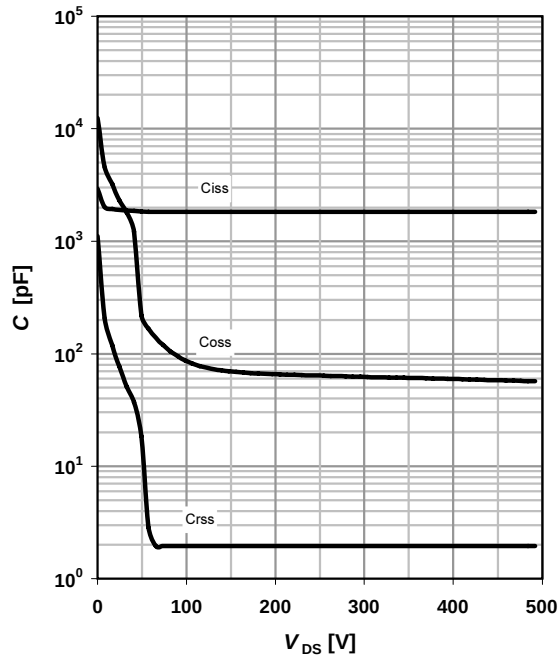
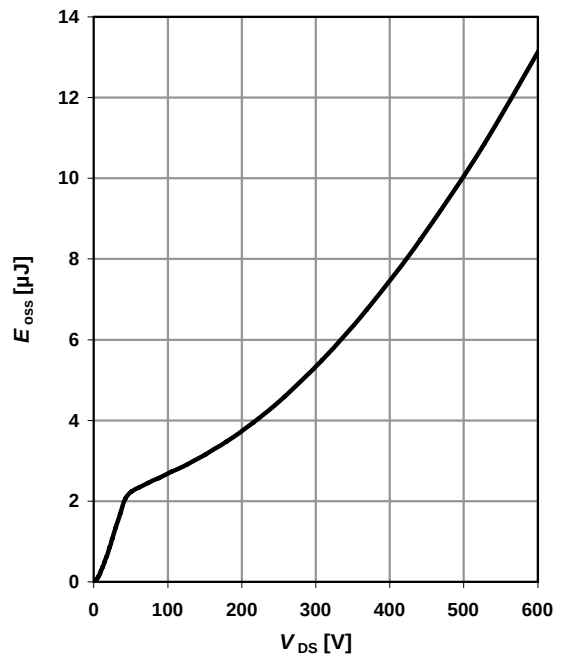
$$E_{AS}=f(T_j); I_D=7.9\text{ A}; V_{DD}=50\text{ V}$$

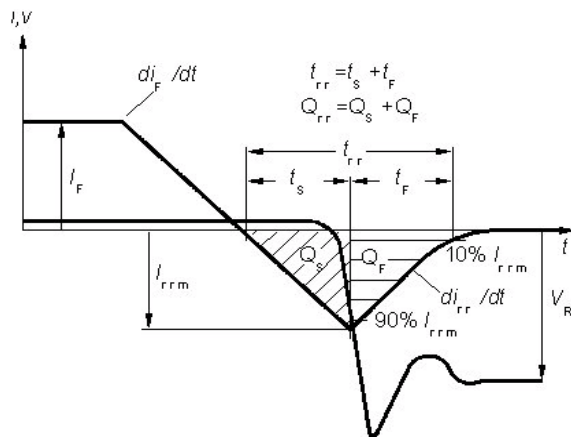


12 Drain-source breakdown voltage

$$V_{BR(DSS)}=f(T_j); I_D=0.25\text{ mA}$$



13 Typ. capacitances
 $C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

14 Typ. Coss stored energy
 $E_{oss} = f(V_{DS})$


Definition of diode switching characteristics


Technical drawing of a mechanical part, showing front, side, and detail views with dimensions and tolerances.

Front View Dimensions:

- A : Distance from the left edge to the center of the top hole.
- E : Total width of the top flange.
- D : Total height of the part.
- $D1$: Height of the main body.
- H : Height of the base.
- L : Length of the base.
- $L1$: Height of the base flange.
- b : Width of the base.
- $b1, b2, b3, b4$: Widths of the base flange features.
- $e, e1$: Distances from the center of the top hole to the edges of the base flange.

Side View Dimensions:

- A : Total width of the part.
- $A1$: Distance from the left edge to the center of the top hole.
- $A2$: Distance from the left edge to the center of the bottom hole.

Detail View Dimensions:

- $\varnothing P$: Diameter of the top hole.
- $\varnothing 0.355(M)$: Diameter of the top hole with tolerance.
- B : Distance from the center of the top hole to the center of the bottom hole.
- $A(M)$: Distance from the center of the top hole to the center of the bottom hole with tolerance.
- $\varnothing 0.381(M)$: Diameter of the bottom hole with tolerance.
- B : Distance from the center of the top hole to the center of the bottom hole.
- $A(M)$: Distance from the center of the top hole to the center of the bottom hole with tolerance.

REFERENCE ...
SCALE 
EUROPEAN PROJECTION 
ISSUE DATE 08-01-2007
FILE T0220_2

Published by
Infineon Technologies AG
81726 Munich, Germany
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